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Why graphene conductivity is constant: scaling theory consideration

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In the recent paper [arXiv: cond-mat/0802.2216, 15 Feb 2008], Kashuba argued that the intrinsic conductivity of graphene independent of temperature originated in strong electron-hole scattering. We propose a much more explicit derivation based on a scaling theory approach. We also give an explanation of a rapid increase in graphene conductivity caused by applied gate voltage.

Experimental investigations of graphene have revealed a quite amazing peculiarity of graphene resistivity. There is almost no dependence of a maximum resistivity of graphene $\rho_{\max}$ on temperature (between $0.3K$ and $300K$) [1]. This is really intriguing because at the same time the carrier density varies by six orders of magnitude.

The maximum resistivity (or intrinsic resistivity) arises at zero gate voltage in a gated graphene structure. The resistivity approximately equals $\rho_{\max} \approx 6kOhm$. There appears a natural temptation to bind this value to two conductance quanta as graphene has a twofold degeneracy of its band structure [1]. The conductance quantum for spin-unpolarized electron gas equals $G_0 = 2e^2/h = (12kOhm)^{-1}$. The obtained $6kOhm$ roughly equals $h/4e^2$, that is, right two conductance quanta. Here we suggest that the coincidence is purely accidental and, actually, $\rho_{\max}$ is determined by electron-hole scattering and bound to the velocity v_{F} characterizing the graphene band-structure and effective permittivity κ_{eff}.

The maximum resistivity (intrinsic resistivity) corresponds to an utterly ambipolar graphene plasma when the electron density Σ_{e} and the hole density Σ_{h} coincide: $\Sigma_{\mathrm{e}} = \Sigma_{\mathrm{h}}$. In the situation the electron-hole scattering is the strongest one.

In the recent paper [2], Kashuba also asserted that the intrinsic conductivity of graphene independent of temperature originated in strong electron-hole scattering. We propose below a much simpler derivation based on scaling theory approach.

The graphene conductivity σ caused by Coulomb scattering among electrons and holes could be plainly supplied by the expression

$$\sigma = \frac{\kappa_{\mathrm{eff}}^2}{e^2} f, \qquad (1)$$

where κ_{eff} is an effective permittivity and f is a so far unknown function of electron-hole system in graphene. In the equation (1) a proper dependence upon the elementary charge e and the effective permittivity κ_{eff} for Born approximation of Coulomb scattering is factorized. As for screening in graphene layer, it was recently theoretically investigated in [3, 4, 5]. This screening turned out to be determined by a weak function of a dimensionless parameter

$$\alpha = \frac{e^2}{\kappa_{\mathrm{eff}} \hbar v_F}. \qquad (2)$$

Here we omit this kind of screening. Really, screening by gates might be substantial were they placed fairly close to a graphene sheet.

The factor f in equation (1) can solely depend on intrinsic graphene parameters and the Plank constant h. In the case when electron and hole densities coincide $\Sigma_{\mathrm{e}} = \Sigma_{\mathrm{h}} = \Sigma_{\mathrm{T}}$ the graphene plasma is fully characterized by an only parameter besides the Fermi velocity v_{F}. It could be a mean momentum p_{T}, or a mean wave vector $k_T = \frac{p_T}{\hbar}$, or temperature $T \approx \frac{\hbar v_F k_T}{k}$ (where k is the Boltzmann constant), or density $\Sigma_T \approx k_T^2$. All those parameters are directly bound to each other. Therefore, the only possible combination looks like

$$\sigma = \frac{\kappa_{\mathrm{eff}}^2 h v_F^2}{e^2} = \frac{2\kappa_{\mathrm{eff}}^2 v_F^2}{G_0}. \qquad (3)$$

Here we neglect a numerical factor of the order of unity which could be derived via thorough consideration of electron-hole scattering [2] or determined from experimental data [1].

The only temperature-dependent parameter k_{T} describing graphene plasma can not be included. Therefore, graphene conductance becomes independent of temperature. Moreover, it is readily seen that the graphene conductivity turned out to be inversely proportional to the conductance quantum $G_0 = 2e^2/h = (13kOhm)^{-1}$, in spite of former expectations [1].

It is expedient to estimate the value of σ for typical graphene structures. When a graphene sheet is sandwiched between two dielectrics with permittivity κ_1 and κ_2, the effective permittivity is

$$\kappa_{\mathrm{eff}} = \frac{\kappa_1 + \kappa_2}{2}. \qquad (4)$$

Therefore, in our opinion, the crucial experiment to verify the above proposed theory lies in changing the permittivity of adjacent dielectrics. In most of so far made

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experiments a graphene layer was deposited on $\mathrm{SiO_2}$ surface. The effective permittivity in the case is equal to $\kappa_{\mathrm{eff}} \approx 2.5$. The velocity $v_{\mathrm{F}} = 10^8 cm/s$ in CGS system of units corresponds to the conductance equal to $(3kOhm)^{-1}$. Substituting all that in equation (3) one obtains $\sigma \approx (4kOhm)^{-1}$. It is a very good agreement with the experimental value equal to $(6kOhm)^{-1}$[1] allowing for a numerical coefficient in relation (3) was ignored.

All said above belongs to an intrinsic graphene conductivity when both electron and hole densities are exactly equal to each other: $\Sigma_{\mathrm{e}} = \Sigma_{\mathrm{h}} = \Sigma_{\mathrm{T}}$. It seems interesting to apprehend what occurs beyond this equality which can be broken by a gate voltage. At fairly high gate voltage when $\Sigma_{\mathrm{e}} \gg \Sigma_{\mathrm{h}}$ or vice versa, the graphene plasma is almost unipolar and electron-hole scattering is no more important. In that case, the conductivity is likely governed by scattering on charged defects [1, 6] as there is no temperature dependence of mobility evidenced by experiments. Obviously, for perfect graphene structure phonon scattering dominates and governs graphene conductivity [7]. Probably, a carrier mobility can achieve values above 200 000 cm^2/Vs instead of nowadays 5 000 − 15 000 cm^2/Vs at room temperature [8].

The explanation of constant value of intrinsic graphene conductivity put forward above implies that the electron-hole scattering predominates over all other mechanisms of scattering even at very low temperature $(1 - 10K)$ when electron and hole density is very small $(10^9 - 10^{10} cm^{-2})$. At first glance, this definitely contradicts another intriguing feature of graphene conductivity observed in experiments [1], namely, a rapid increase in graphene conductivity with rising gate voltage. The defect concentration consistent with measured values of mobility in the range of 5 000 − 15 000 cm^2/Vs was estimated as 10^{12} cm^{-2} [1]. To cope with this contradiction we suggest that charged defect concentration depends on position of the Fermi level in graphene, or the Fermi energy ε_F. For instance, such defects may arise at the graphene/$\mathrm{SiO_2}$ interface. If number of defects per unit energy and area is constant and equals n_i their space concentration is

$$\Sigma_i = n_i \varepsilon_F \approx n_i v_F \hbar \sqrt{\Sigma}, \tag{5}$$

where Σ is a majority carrier density (electrons or holes). For intrinsic graphene state the Fermi energy in the relation (5) should be replaced by thermal energy kT. This supposition substantiates that charged defect density can be smaller than that of carriers even at low temperatures.

In conclusion, we assert that maximum (intrinsic) resistivity of graphene originates in a strong electron-hole scattering when both electron and hole densities coincide. It does not depend on temperature and can be manipulated by permittivity of surrounding dielectrics and screening of metallic gates.

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